

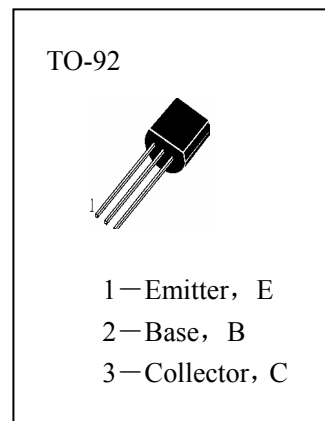


PNP EPITAXIAL SILICON TRANSISTOR

2W OUTPUT AMPLIFIER OF PORTABLE RADIOS IN CLASS B PUSH-PULL OPERATION.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

- Tstg—Storage Temperature... -55~150°C
Tj—Junction Temperature... 150°C
Pc—Collector Dissipation... 1W
Vcbo—Collector-Base Voltage... -40V
Vceo—Collector-Emitter Voltage... -25V
Veb0—Emitter-Base Voltage... -6V
Ic—Collector Current... -1.5A



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Table with 7 columns: Symbol, Characteristics, Min, Typ, Max, Unit, Test Conditions. Rows include ICBO, IEBO, HFE (1), HFE (2), VBE, VCE(sat), VBE(sat), BVcbo, BVceo, BVebo, Cob, and ft.

hFE Classification

Table with 4 columns: B, C, D, E. Rows show hFE ranges: 85-160, 120-200, 160-300, 270-500.



### Typical Characteristics

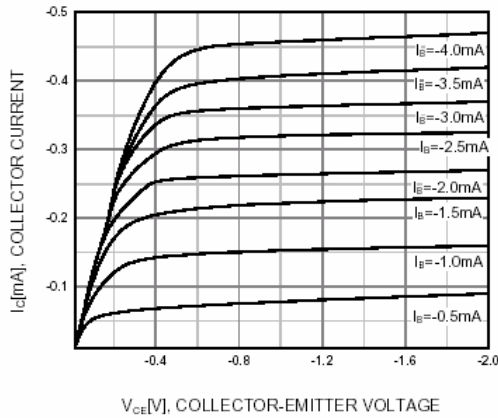


Figure 1. Static Characteristic

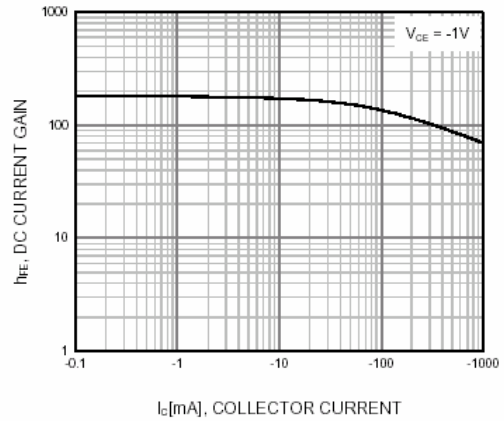


Figure 2. DC current Gain

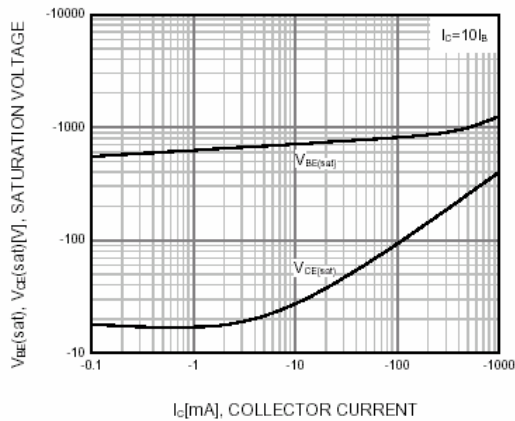


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

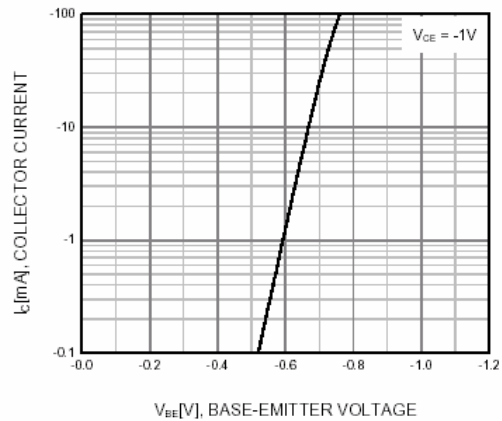


Figure 4. Base-Emitter On Voltage

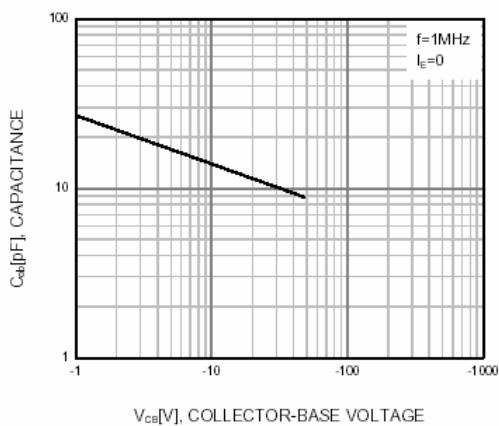


Figure 5. Collector Output Capacitance

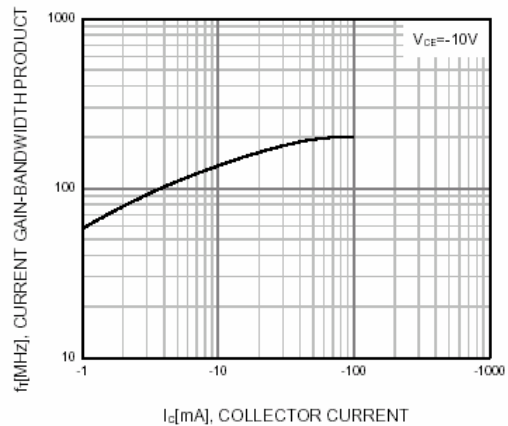


Figure 6. Current Gain Bandwidth Product